

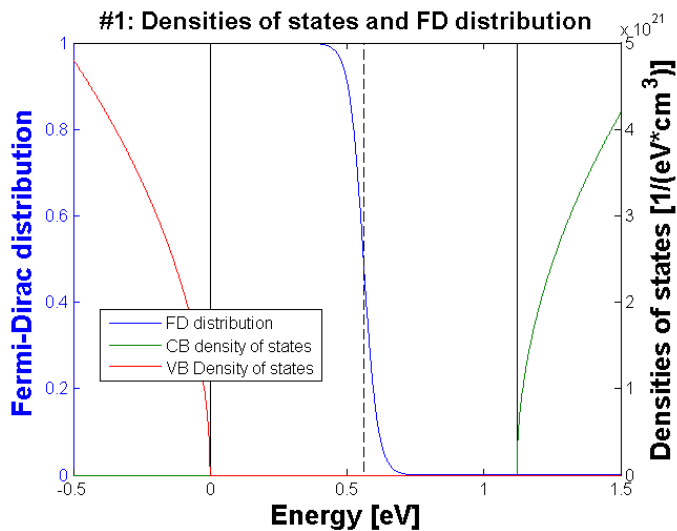
# TN2624 MATLAB Session 11

## Solutions

May 23, 2013

### Semiconductor statistics Part 1 – the intrinsic semiconductor (60 pts)

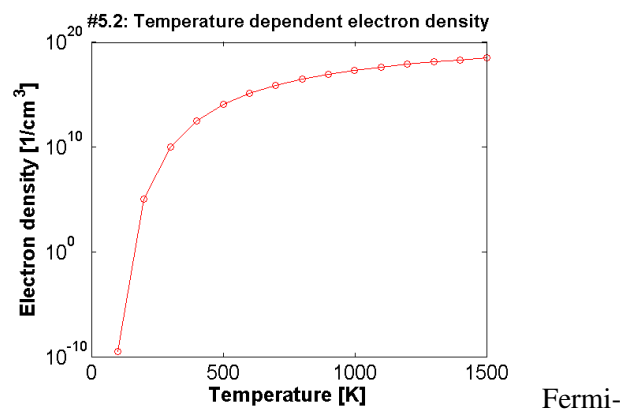
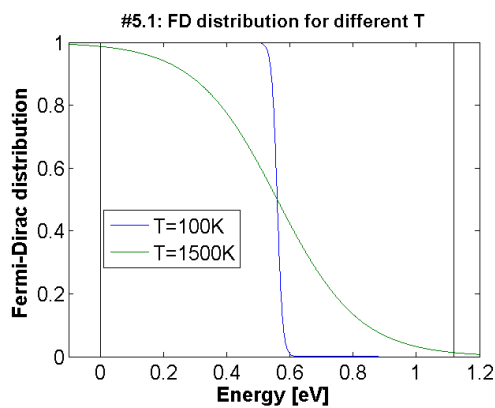
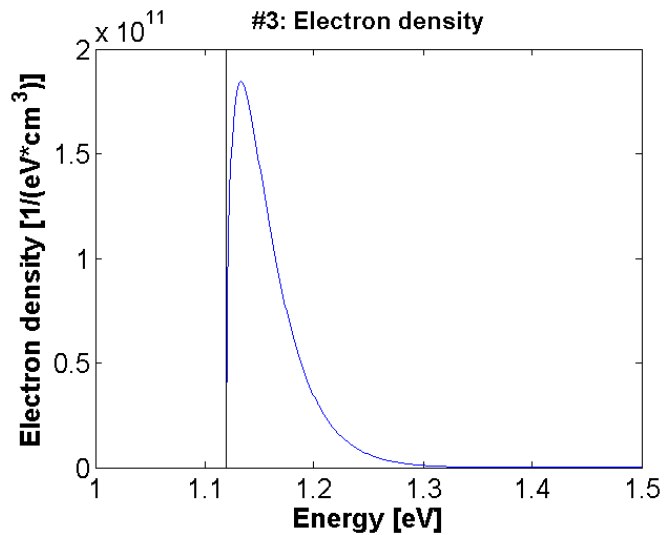
1. (25 pts) Fermi-Dirac distribution and density of states as a function of energy.



2. (5 pts) The same as the distribution for the electrons, but mirrored at the chemical potential

$$\bar{n}_{\text{FD,h}}(E) = \frac{1}{1 + \exp \frac{\mu - E}{kT}}.$$

3. (10 pts)
4. (5 pts) %Result:  $9.8506 \times 10^9 \text{ 1/cm}^3$ , way too low
5. (25 pts)

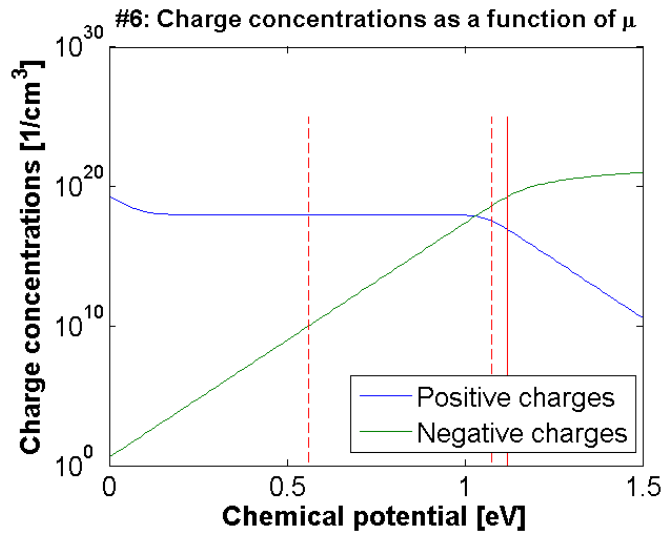


Dirac distribution “smears out” at higher temperatures → more electrons excited to the conduction band

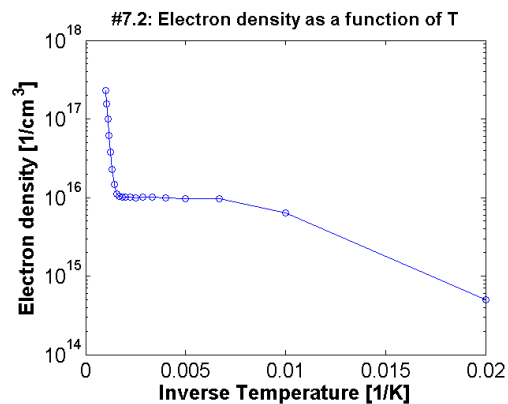
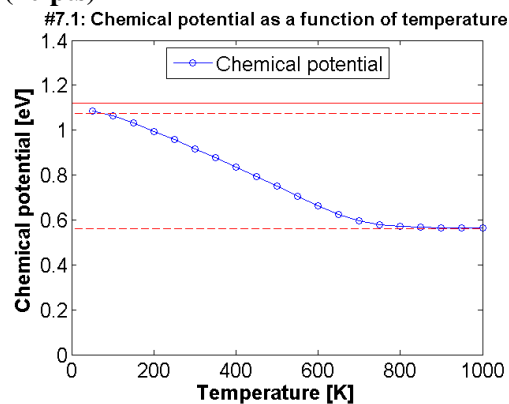
Unrealistically high temperatures would be required to obtain significant electron densities

## Semiconductor statistics Part 2 – the doped semiconductor (40 pts)

6. (20 pts)  $\mu = 1.0300 \text{ eV}$ ,  $n = 7.6210 \times 10^{17} \text{ cm}^{-3}$ ,  $p = 1.2597 \times 10^{-4} \text{ cm}^{-3}$ , virtually no holes in the valence band... all electrons stem from the dopants



7. (10 pts)



- Low temperature: The electrons from the dopants get excited to the conduction band
- Medium temperature: All the dopants have been activated (electron density saturates to dopant density), yet the temperature is still too low to excite electrons from the valence band to the conduction band
- High temperature: Electrons can be excited from the valence band to the conduction band